



ABSTRACT OF THE DISCLOSURE

A semiconductor device has a semiconductor substrate having a first conductivity type, a gate insulating film disposed on a surface of the semiconductor substrate, and a gate electrode disposed on the gate insulating film. Low concentration diffusion layers are disposed on the surface of the semiconductor substrate on opposite sides of the gate electrode. The low concentration diffusion layers have a second conductivity type different from the first conductivity type. An interlayer film is disposed over the semiconductor substrate for electrically isolating the gate electrode and the low concentration diffusion layers from wiring disposed on the interlayer film. Contact holes extend through the interlayer film for electrically connecting the gate electrode and the low concentration diffusion layers with the wirings disposed on the interlayer film. High concentration diffusion layers have the second conductivity type and are disposed only in portions of the respective low concentration diffusion layers directly under the respective contact holes.